## IAP5 Rec'd PCT/PTO 01 FEB 2006 10/567729 OGOSH46USA

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re t	he Application of:	)
		) Examiner:
	Kazutoshi Kojima et al.	)
		) Group Art Unit:
Application No.:		)
		)
Corresponding International Filing No.:		)
	PCT/JP2004/011894	)
		)
Filed:	Herewith	)
		)
For:	SILICON CARBIDE EPITAXIAL	.)
	WAFER, METHOD FOR	)
	PRODUCING SUCH WAFER,	)
	AND SEMICONDUCTOR	)
	DEVICE FORMED ON SUCH	)
	WAFER	)

Mail Stop PCT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

## FIRST PRELIMINARY AMENDMENT

Sir:

Before calculating the filing fee, please amend the above-identified patent application as follows.

Amendments to the Claims are reflected in the listing of claims which begins on page two of this paper.

Remarks begin on page three of this paper.